

11th International Conference on Atomically Controlled Surfaces, Interfaces and Nanostructures



October 3-7, 2011
St. Petersburg, Russia

www.acsin11.com

First Announcement

:::About ACSIN:::

The First International Symposium on Atomically Controlled Surfaces and Interfaces was held in Tokyo (1991). Bearing in mind the recent developments in nanoscience and nanotechnology, the word "Nanostructures" has been added to the name of the conference since the Fifth International Conference on Atomically Controlled Surfaces, Interfaces and Nanostructures (ACSIN-5) was held in Aix-en-Provence in 1999.

Following the successful series of ACSIN conferences in Tokyo (ACSIN-9, 2007) and Granada (ACSIN-10, 2009), this conference aims to present new concepts, techniques and applications of atomically controlled processes at surfaces, interfaces and nanostructures.

The conference is open for scientists and engineers in the fields of condensed matter physics, inorganic and organic chemistry, and biology.

The conference will be organized in sections with key lectures given by a limited number of invited speakers on topics of relevant scientific and technological interest. Poster sessions will also be held during the conference.

The official language of the conference will be English.

:::Venue:::

The Conference will be held in St. Petersburg, one of the main cultural, historical and architectural centers of Russia. Interesting social program and excursions are planned for participants and accompanying persons. To visit Russian Federation an entry visa is required.

:::Main Topics:::

The following main topics include, but are not limited to:

- ⊙ Aromatic and Biomimetic Organic Arrays
- ⊙ Atomic and Molecular Manipulation
- ⊙ Carbon Related Nanomaterials: Nanotubes and Graphene
- ⊙ Characterization and Instrumentation
- ⊙ Electronic Transport
- ⊙ Nano-Biotechnology
- ⊙ Nano-Electronics and Molecular-Based Devices
- ⊙ Nano-Magnetism
- ⊙ Nanoparticles and clusters
- ⊙ Nano-Photonics
- ⊙ Organic Thin Film Devices
- ⊙ Oxides
- ⊙ Reaction and Dynamics
- ⊙ Scanning Probe Microscopy
- ⊙ Surface Microscopy
- ⊙ Surfaces and Interfaces: Atomic Structure
- ⊙ Surfaces and Interfaces: Electronic Properties
- ⊙ Thin Film Growth and Application



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::Key Dates::

March 1, 2011 – Abstract submission

May 1, 2011 – Notification of acceptance

July 1, 2011 – Regular registration

October 3 - 7, 2011 – Conference

::Abstract::

Abstracts should be submitted electronically over the web-page by March 1, 2011.

Abstracts should not exceed 300 words. You may specify whether you would prefer to present your work in the form of a poster or as an oral presentation. The final decision, however, will be made by the program committee. You will be notified of the acceptance by May 1, 2011.

::Proceedings::

ACSIN-11 proceedings are planned to be published by the e-Journal of Surface Science and Nanotechnology.

::Contacts::

Do not hesitate to contact us for further information: info@acsin11.com.

